ESH2PB, ESH2PC & ESH2PD



Vishay General Semiconductor

High Current Density Surface Mount Ultrafast Rectifiers



DO-220AA (SMP)

PRIMARY CHARACTERISTICS				
I _{F(AV)}	2 A			
V _{RRM}	100 V, 150 V, 200 V			
t _{rr}	25 ns			
V_F at $I_F = 2 A$	0.75 V			
T _J max.	175 °C			

FEATURES





· Ideal for automated placement

• Glass passivated chip junction

(e3)

• Ultrafast recovery times for high frequency

RoHS

Low forward voltage drop, low power loss

· Low thermal resistance

- Meets MSL level 1 pe r J-STD-020, LF ma ximum peak of 260 °C
- Component in accor dance to Ro HS 20 02/95/EC and WEEE 2002/96/EC

TYPICAL APPLICATIONS

For use in secondary rectification and freewheeling for ultrafast swit ching spe eds of a c-to-ac and dc-to-dc converters in high temperature conditions for both consumer and automotive applications.

MECHANICAL DATA

Case: DO-220AA (SMP)

Epoxy meets UL 94V-0 flammability rating

Terminals: Matte t in pla ted lead s, so Iderable pe r

J-STD-002 and JESD22-B102

E3 suffix for consumer grade, meets JESD 201 class 1A whis ker test, HE3 suffix for high reliability grade (AEC Q1 01 qualified), m eets JESD 20 1 class 2

whisker test

Polarity: Color band denotes cathode end

MAXIMUM RATINGS (T _A = 25 °C unless otherwise noted)					
PARAMETER	SYMBOL	ESH2PB	ESH2PC	ESH2PD	UNIT
Device marking code		P2B	P2C	P2D	
Maximum repetitive peak reverse voltage	V_{RRM}	100 150 20	00		V
Maximum average forward rectified current (Fig. 1)	I _{F(AV)} 2.	0			Α
Peak forward surge current 10 ms single half sine-wave superimposed on rated load	I _{FSM} 50				А
Operating junction and storage temperature range	T _J , T _{STG}	- 55 to + 175			°C

ELECTRICAL CHARACTERISTICS (T _A = 25 °C unless otherwise noted)						
PARAMETER	TEST CONDITIONS		SYMBOL	TYP.	MAX.	UNIT
Maximum instantaneous forward voltage (1)	I _F = 2 A	T _J = 25 °C T _J = 125 °C	V _F	0.90 0.75	0.98 0.82	٧
Maximum reverse current (2)	rated V _R	T _J = 25 °C T _J = 125 °C	I _R	0.2 12.6	1.0 25	μΑ

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ELECTRICAL CHARACTERISTICS (T _A = 25 °C unless otherwise noted)						
PARAMETER	TEST CONDITIONS		SYMBOL	TYP.	MAX.	UNIT
Maximum reverse recovery time	I _F = 0.5 A, I _R = 1 A, I _{rr} = 0.25 A		t _{rr}	-	25 ns	
Typical reverse recovery time	I _F = 1.0 A, V _R = 30 V, dI/dt = 50 A/μs,	T _J = 25 °C T _J = 100 °C	t _{rr}	-	25 35	ns
Typical stored charge	$I_{rr} = 10 \% I_{RM}$		Q _{rr}	- -	10 15	nC
Typical junction capacitance	4.0 V, 1 MHz		C _J -2		5	pF

Notes:

(1) Pulse test: 300 μs pulse width, 1 % duty cycle

(2) Pulse test: Pulse width ≤ 40 ms

THERMAL CHARACTERISTICS (T _A = 25 °C unless otherwise noted)					
PARAMETER	SYMBOL	ESH2PB	ESH2PC	ESH2PD	UNIT
Typical thermal resistance ⁽¹⁾	$egin{array}{l} R_{ hetaJA} \ R_{ hetaJL} \ R_{ hetaJC} \end{array}$		80 15 22		°C/W

Note:

(1) Thermal resistance from junction to ambient and junction to lead mounted on P.C.B. with 6.0 x 6.0 mm copper pad areas. $R_{\theta JL}$ is measured at the terminal of cathode band. $R_{\theta JC}$ is measured at the top centre of the body

ORDERING INFORMATION (Example)						
PREFERRED P/N	UNIT WEIGHT (g)	PREFERRED PACKAGE CODE	BASE QUANTITY	DELIVERY MODE		
ESH2PB-E3/84A	0.024	84A	3000	7" diameter plastic tape and reel		
ESH2PB-E3/85A	0.024	85A	10 000	13" diameter plastic tape and reel		
ESH2PBHE3/84A (1)	0.024	84A	3000	7" diameter plastic tape and reel		
ESH2PBHE3/85A (1)	0.024	85A	10 000	13" diameter plastic tape and reel		

Note:

(1) Automotive grade AEC Q101 qualified

RATINGS AND CHARACTERISTICS CURVES

(T_A = 25 °C unless otherwise noted)

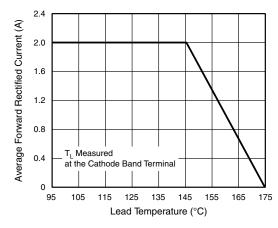


Figure 1. Forward Current Derating Curve

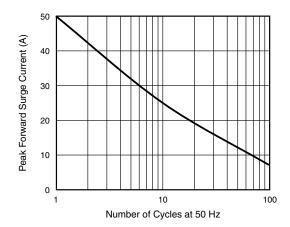


Figure 2. Maximum Non-Repetitive Peak Forward Surge Current





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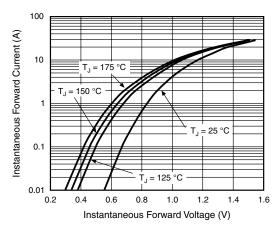


Figure 3. Typical Instantaneous Forward Characteristics

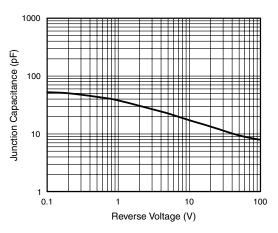


Figure 5. Typical Junction Capacitance

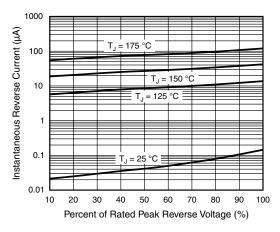


Figure 4. Typical Reverse Leakage Characteristics

PACKAGE OUTLINE DIMENSIONS in inches (millimeters)

DO-220AA (SMP) 0.012 (0.30) REF. Cathode band 9<u>0</u> 0.086 (2.18) 0.053 (1.35) 0.036 (0.91) 0.074 (1.88) 0.041 (1.05) 0.024 (0.61) 0.142 (3.61) 0.103 (2.60) 0.032 (0.80) 0.126 (3.19) 0.087 (2.20) 0.016 (0.40) 0.158 (4.00) 0.146 (3.70) 0.025 0.030 (0.635) (0.762) 0.105 0.013 (0.35) 0.004 (0.10) 0.045 (1.15) 0.033 (0.85) 0.100 (2.54) 0.050 (1.27) 0.012 (0.30) 0.018 (0.45) 0.000 (0.00) 0.006 (0.15)



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